

## LSU403 N-CHANNEL JFET



## Linear Systems replaces discontinued Siliconix U403

The LSU403 is a Low Noise, Low Drift, Monolithic Dual N-Channel JFET

The LSU403 is a high-performance monolithic dual JFET featuring extremely low noise, tight offset voltage and low drift over temperature specifications, and is targeted for use in a wide range of precision instrumentation applications. The LSU403 features a 5mV offset and  $10-\mu\text{V}/^{\circ}\text{C}$  drift. The LSU403 is a direct replacement for discontinued Siliconix LSU403.

The 6 Pin SOT-23 provides a low cost option and ease of manufacturing.

(See Packaging Information).

## LSU403 Applications:

- Wideband Differential Amps
- High-Speed, Temp-Compensated Single-Ended Input Amps
- **High-Speed Comparators**
- Impedance Converters and vibrations detectors.

FEATURES							
LOW DRIFT		$ V_{GS1-2}/T  = 10\mu V/^{\circ}C$ TYP.					
LOW NOISE		$e_n = 6nV/Hz @ 10Hz TYP.$					
LOW PINCHOFF		$V_p = 2.5V \text{ TYP}.$					
ABSOLUTE MAXIMUM RATINGS							
@ 25°C (unless otherwise noted)							
Maximum Temperatures							
Storage Ten	nperature		-65°C to +150°C				
Operating Ju	unction Temperature		+150°C				
Maximum Voltage and Current for Each Transistor – Note 1							
-V <sub>GSS</sub>	Gate Voltage to Drain or Source		50V				
-V <sub>DSO</sub>	Drain to Source Voltage		50V				
-I <sub>G(f)</sub>	Gate Forward Current	10mA					
Maximum Power Dissipation							
Device Dissipation @ Free Air – Total 300mW							

MATCHING CHARAC	ATCHING CHARACTERISTICS @ 25°C UNLESS OTHERWISE NOTED					
SYMBOL	CHARACTERISTICS	VALUE	UNITS	CONDITIONS		
V <sub>GS1-2</sub> / T  max.	DRIFT VS.	25	μV/°C	$V_{DG}$ =10V, $I_{D}$ =200 $\mu$ A		
	TEMPERATURE			T <sub>A</sub> =-55°C to +125°C		
V <sub>GS1-2</sub>   max.	OFFSET VOLTAGE	10	mV	$V_{DG}$ =10V, $I_{D}$ =200 $\mu$ A		

ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted) CONDITIONS **SYMBOL** CHARACTERISTICS MIN TYP. MAX. UNITS BV<sub>GSS</sub> I<sub>D</sub>=1nA Breakdown Voltage 50 60  $V_{DS} = 0$ Gate-To-Gate Breakdown \_\_ ±50 ٧  $BV_{GGO}$  $I_D = 0$  $I_s = 0$  $I_G = 1nA$ TRANSCONDUCTANCE 2000 Full Conduction 7000 f = 1kHz 10\/ umho  $I_D = 200 \mu A$  f = 1kHzTypica<mark>l O</mark>per<mark>at</mark>ion 1000 2000 μmho 15V Mismatch 0.6 3 %  $|Y_{FS1-2}/Y_{FS}|$ **DRAIN CURRENT**  $V_{DG}$ = 10V10 V<sub>GS</sub>= 0V **Full Conduction** 0.5 mA Mismatch at Full Conduction 1  $|I_{DSS1-2}/I_{DSS}|$ 5 % **GATE VOLTAGE** Pinchoff voltage  $V_{GS}(off)$  or  $V_{r}$ -0.5 -2.5  $V_{DS} = 15V$  $I_D = 1nA$  $V_{GS}(on)$ **Operating Range** -2.3 ٧  $V_{DS}=15V$  $I_D = 200 \mu A$ **GATE CURRENT**  $V_{DG} = 15V I_D = 200 \mu A$ -I<sub>G</sub>max. Operating -4 -15 pΑ  $T_A = +125$ °C -I<sub>G</sub>max. High Temperature -10 nΑ -l<sub>GSS</sub>max. At Full Conduction 100 рΑ  $V_{DS} = 0$ -I<sub>GSS</sub>max. High Temperature 5  $V_{DG} = 15V$ T<sub>A</sub>= +125°C 5 5 рΑ **OUTPUT CONDUCTANCE Full Conduction** V<sub>DG</sub>= 10V Yoss 20 μmho  $V_{GS} = 0V$  $Y_{\underline{OS}}$ Operating 0.2 2 umho  $V_{DG} = 15V$  $I_{D} = 500 \mu A$ **COMMON MODE REJECTION**  $V_{DS} = 10 \text{ to } 20V$ **CMR** -20 log | V <sub>GS1-2</sub>/ V <sub>DS</sub>| 95 dB  $I_D = 30 \mu A$ **NOISE**  $V_{DS} = 15V$  $V_{GS} = 0V$  $R_G = 10M$ NF **Figure** 0.5 dB f= 100Hz NBW= 6Hz  $V_{DS}$ =15V  $I_D$ =200 $\mu$ A f=10Hz NBW=1Hz e<sub>n</sub> Voltage 20 nV/√Hz **CAPACITANCE**  $\mathbf{C}_{\underline{\text{ISS}}}$ Input 8 рF  $V_{DS} = 15V$   $I_{D} = 200 \mu A$ f= 1MHz рF Reverse Transfer 1.5  $C_{RSS}$ 

Note 1 - These ratings are limiting values above which the serviceability of any semiconductor may be impaired

Available Packages:

LSU403 in SOT-23

LSU403 available as bare die

Please contact Micross for full package and die dimensions

SOT-23 **TOP VIEW** 圓 S2 G1 [[1 D1 12 5∐ D2 4]] G2 S1 II3

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